Lattice Semiconductor Corporation - LCMXO3L-4300E-5UWG81ITR Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	540
Number of Logic Elements/Cells	4320
Total RAM Bits	94208
Number of I/O	63
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	81-UFBGA, WLCSP
Supplier Device Package	81-WLCSP (3.80x3.69)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo3l-4300e-5uwg81itr

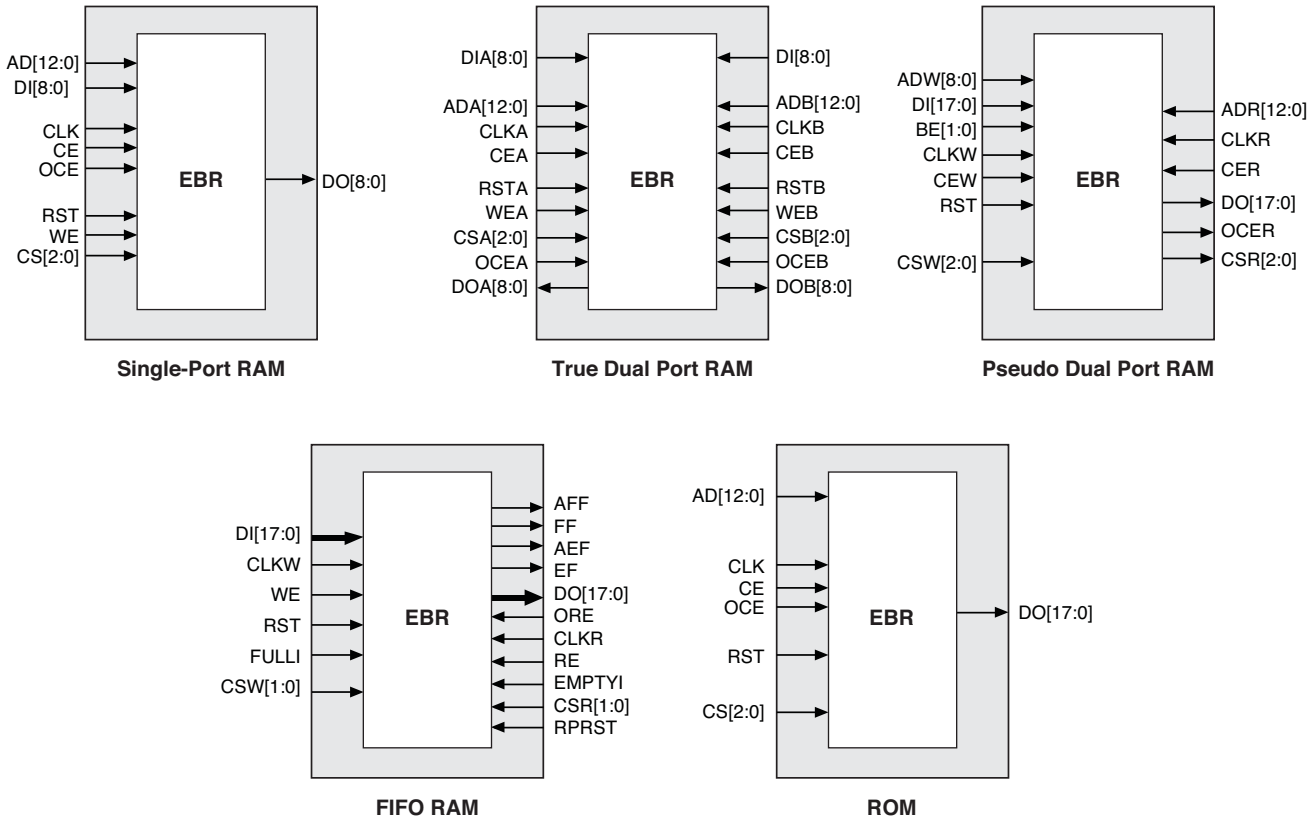
MachXO3 Family Data Sheet Introduction

January 2016 Advance Data Sheet DS1047

Features

- **Solutions**
  - Smallest footprint, lowest power, high data throughput bridging solutions for mobile applications
  - Optimized footprint, logic density, IO count, IO performance devices for IO management and logic applications
  - High IO/logic, lowest cost/IO, high IO devices for IO expansion applications
- **Flexible Architecture**
  - Logic Density ranging from 640 to 9.4K LUT4
  - High IO to LUT ratio with up to 384 IO pins
- **Advanced Packaging**
  - 0.4 mm pitch: 1K to 4K densities in very small footprint WLCSP (2.5 mm x 2.5 mm to 3.8 mm x 3.8 mm) with 28 to 63 IOs
  - 0.5 mm pitch: 640 to 6.9K LUT densities in 6 mm x 6 mm to 10 mm x 10 mm BGA packages with up to 281 IOs
  - 0.8 mm pitch: 1K to 9.4K densities with up to 384 IOs in BGA packages
- **Pre-Engineered Source Synchronous I/O**
  - DDR registers in I/O cells
  - Dedicated gearing logic
  - 7:1 Gearing for Display I/Os
  - Generic DDR, DDRx2, DDRx4
- **High Performance, Flexible I/O Buffer**
  - Programmable sysIO™ buffer supports wide range of interfaces:
    - — LVCMOS 3.3/2.5/1.8/1.5/1.2
    - — LVTTL
    - — LVDS, Bus-LVDS, MLVDS, LVPECL
    - — MIPI D-PHY Emulated
    - — Schmitt trigger inputs, up to 0.5 V hysteresis
  - Ideal for IO bridging applications
  - I/Os support hot socketing
  - On-chip differential termination
  - Programmable pull-up or pull-down mode
- **Flexible On-Chip Clocking**
  - Eight primary clocks
  - Up to two edge clocks for high-speed I/O interfaces (top and bottom sides only)
  - Up to two analog PLLs per device with fractional-n frequency synthesis
    - — Wide input frequency range (7 MHz to 400 MHz)
- **Non-volatile, Multi-time Programmable**
  - Instant-on
    - — Powers up in microseconds
  - Optional dual boot with external SPI memory
  - Single-chip, secure solution
  - Programmable through JTAG, SPI or I^2C
  - MachXO3L includes multi-time programmable NVCM
  - MachXO3LF infinitely reconfigurable Flash
    - — Supports background programming of non-volatile memory
- **TransFR Reconfiguration**
  - In-field logic update while IO holds the system state
- **Enhanced System Level Support**
  - On-chip hardened functions: SPI, I^2C, timer/counter
  - On-chip oscillator with 5.5% accuracy
  - Unique TraceID for system tracking
  - Single power supply with extended operating range
  - IEEE Standard 1149.1 boundary scan
  - IEEE 1532 compliant in-system programming
- **Applications**
  - Consumer Electronics
  - Compute and Storage
  - Wireless Communications
  - Industrial Control Systems
  - Automotive System
- **Low Cost Migration Path**
  - Migration from the Flash based MachXO3LF to the NVCM based MachXO3L
  - Pin compatible and equivalent timing

Figure 2-8. sysMEM Memory Primitives

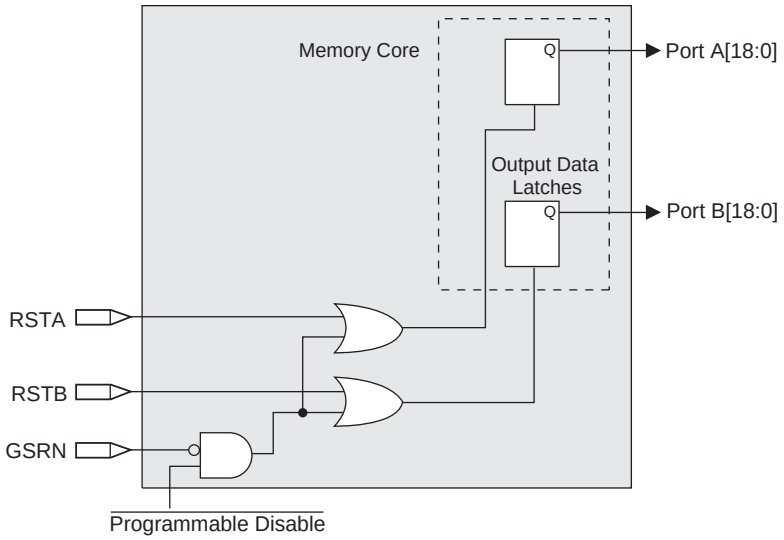


state. The RPRST signal is used to reset the read pointer. The purpose of this reset is to retransmit the data that is in the FIFO. In these applications it is important to keep careful track of when a packet is written into or read from the FIFO.

Memory Core Reset

The memory core contains data output latches for ports A and B. These are simple latches that can be reset synchronously or asynchronously. RSTA and RSTB are local signals, which reset the output latches associated with port A and port B respectively. The Global Reset (GSRN) signal resets both ports. The output data latches and associated resets for both ports are as shown in Figure 2-9.

Figure 2-9. Memory Core Reset

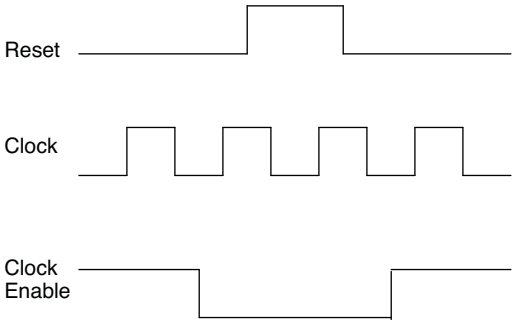


For further information on the sysMEM EBR block, please refer to TN1290, Memory Usage Guide for MachXO3 Devices.

EBR Asynchronous Reset

EBR asynchronous reset or GSR (if used) can only be applied if all clock enables are low for a clock cycle before the reset is applied and released a clock cycle after the reset is released, as shown in Figure 2-10. The GSR input to the EBR is always asynchronous.

Figure 2-10. EBR Asynchronous Reset (Including GSR) Timing Diagram



If all clock enables remain enabled, the EBR asynchronous reset or GSR may only be applied and released after the EBR read and write clock inputs are in a steady state condition for a minimum of $1/f_{MAX}$ (EBR clock). The reset release must adhere to the EBR synchronous reset setup time before the next active read or write clock edge.

Output Register Block

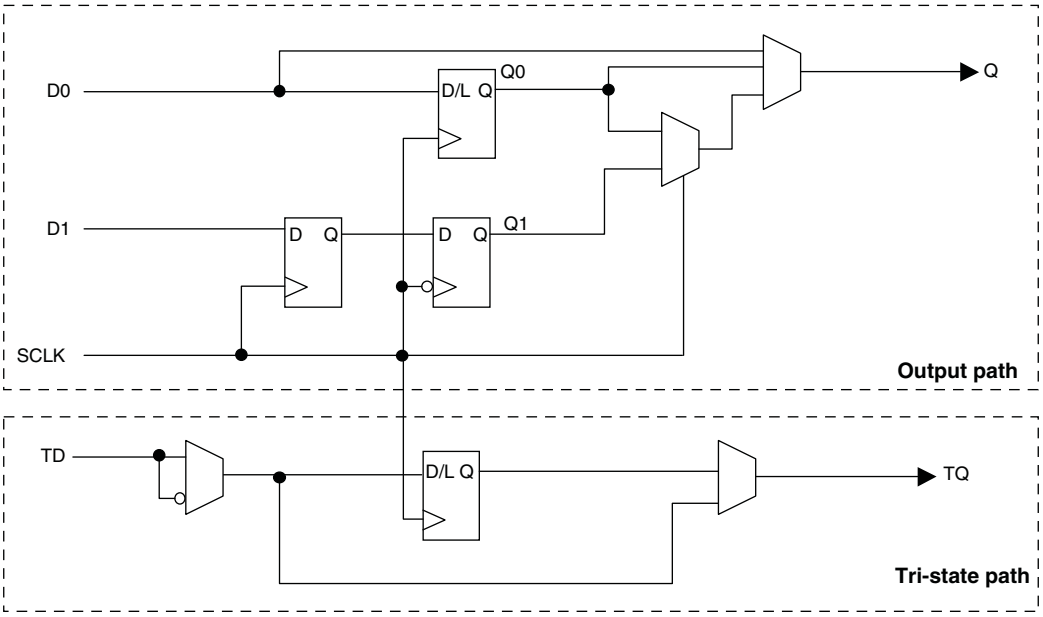
The output register block registers signals from the core of the device before they are passed to the sysIO buffers.

Left, Top, Bottom Edges
In SDR mode, D0 feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as a D-type register or latch.

In DDR generic mode, D0 and D1 inputs are fed into registers on the positive edge of the clock. At the next falling edge the registered D1 input is registered into the register Q1. A multiplexer running off the same clock is used to switch the mux between the outputs of registers Q0 and Q1 that will then feed the output.

Figure 2-12 shows the output register block on the left, top and bottom edges.

Figure 2-12. MachXO3L/LF Output Register Block Diagram (PIO on the Left, Top and Bottom Edges)



Tri-state Register Block

The tri-state register block registers tri-state control signals from the core of the device before they are passed to the sysIO buffers. The block contains a register for SDR operation. In SDR, TD input feeds one of the flip-flops that then feeds the output.

Input Gearbox

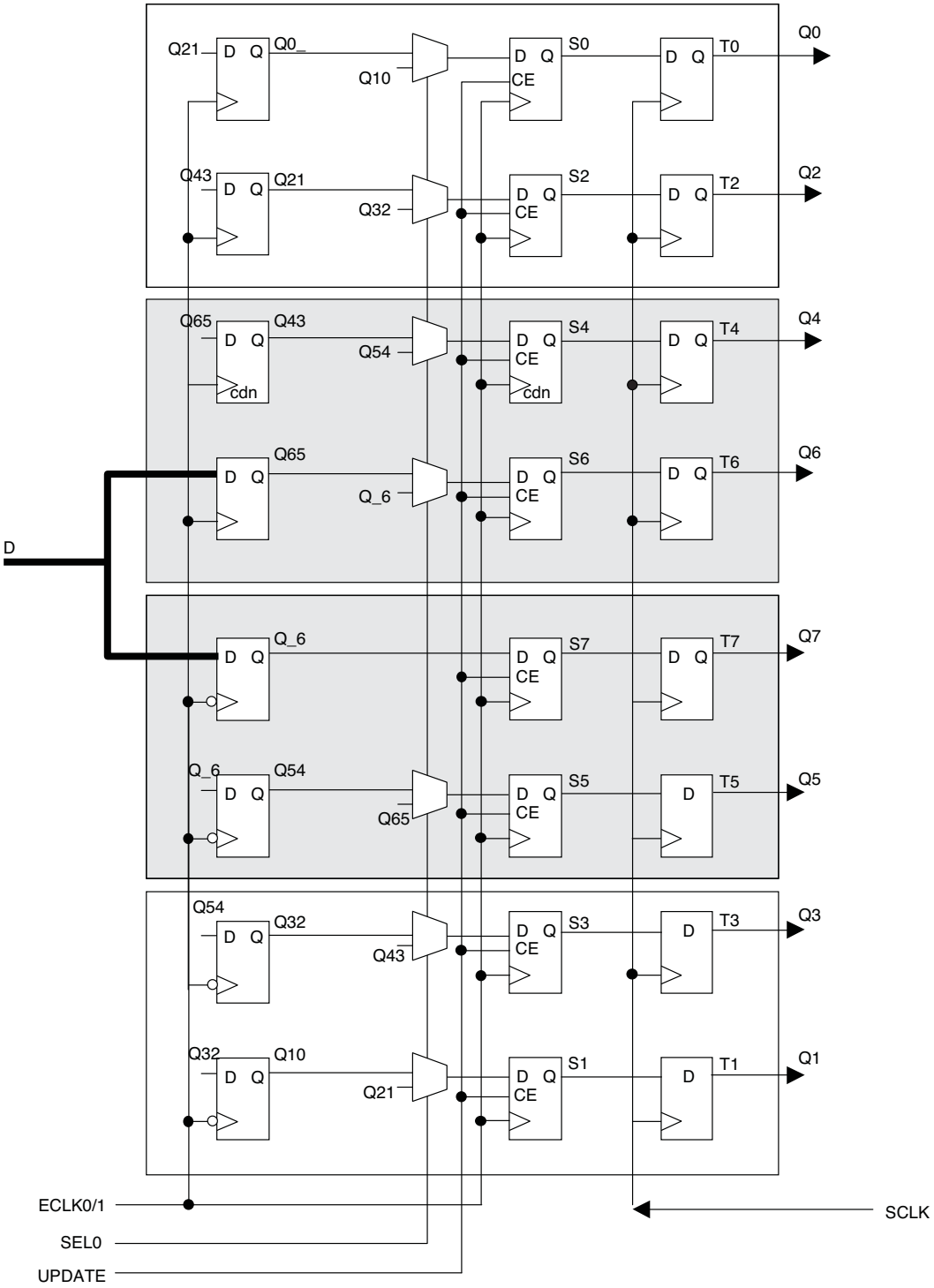
Each PIC on the bottom edge has a built-in 1:8 input gearbox. Each of these input gearboxes may be programmed as a 1:7 de-serializer or as one IDDRX4 (1:8) gearbox or as two IDDRX2 (1:4) gearboxes. Table 2-9 shows the gearbox signals.

Table 2-9. Input Gearbox Signal List

Name	I/O Type	Description
D	Input	High-speed data input after programmable delay in PIO A input register block
ALIGNWD	Input	Data alignment signal from device core
SCLK	Input	Slow-speed system clock
ECLK[1:0]	Input	High-speed edge clock
RST	Input	Reset
Q[7:0]	Output	Low-speed data to device core: Video RX(1:7): Q[6:0] GDDRX4(1:8): Q[7:0] GDDRX2(1:4)(IOL-A): Q4, Q5, Q6, Q7 GDDRX2(1:4)(IOL-C): Q0, Q1, Q2, Q3

These gearboxes have three stage pipeline registers. The first stage registers sample the high-speed input data by the high-speed edge clock on its rising and falling edges. The second stage registers perform data alignment based on the control signals UPDATE and SEL0 from the control block. The third stage pipeline registers pass the data to the device core synchronized to the low-speed system clock. Figure 2-13 shows a block diagram of the input gearbox.

Figure 2-13. Input Gearbox



More information on the input gearbox is available in TN1281, Implementing High-Speed Interfaces with MachXO3 Devices.

Output Gearbox

Each PIC on the top edge has a built-in 8:1 output gearbox. Each of these output gearboxes may be programmed as a 7:1 serializer or as one ODDRX4 (8:1) gearbox or as two ODDRX2 (4:1) gearboxes. Table 2-10 shows the gearbox signals.

Table 2-10. Output Gearbox Signal List

Name	I/O Type	Description
Q	Output	High-speed data output
D[7:0]	Input	Low-speed data from device core
Video TX(7:1): D[6:0]		
GDDRX4(8:1): D[7:0]		
GDDRX2(4:1)(IOL-A): D[3:0]		
GDDRX2(4:1)(IOL-C): D[7:4]		
SCLK	Input	Slow-speed system clock
ECLK [1:0]	Input	High-speed edge clock
RST	Input	Reset

The gearboxes have three stage pipeline registers. The first stage registers sample the low-speed input data on the low-speed system clock. The second stage registers transfer data from the low-speed clock registers to the high-speed clock registers. The third stage pipeline registers controlled by high-speed edge clock shift and mux the high-speed data out to the sysIO buffer. Figure 2-14 shows the output gearbox block diagram.

Table 2-11 shows the I/O standards (together with their supply and reference voltages) supported by the MachXO3L/LF devices. For further information on utilizing the sysIO buffer to support a variety of standards please see TN1280, MachXO3 sysIO Usage Guide.

Table 2-11. Supported Input Standards

	VCCIO (Typ.)				
Input Standard	**3.3 V**	**2.5 V**	**1.8 V**	**1.5 V**	**1.2 V**
Single-Ended Interfaces					
LVTTL	Yes				
LVCMOS33	Yes				
LVCMOS25		Yes			
LVCMOS18			Yes		
LVCMOS15				Yes	
LVCMOS12					Yes
PCI	Yes				
Differential Interfaces					
LVDS	Yes	Yes			
BLVDS, MLVDS, LVPECL, RSDS	Yes	Yes			
MIPI[1]	Yes	Yes			
LVTTLD	Yes				
LVCMOS33D	Yes				
LVCMOS25D		Yes			
LVCMOS18D			Yes		

1. These interfaces can be emulated with external resistors in all devices.

TraceID

Each MachXO3L/LF device contains a unique (per device), TraceID that can be used for tracking purposes or for IP security applications. The TraceID is 64 bits long. Eight out of 64 bits are user-programmable, the remaining 56 bits are factory-programmed. The TraceID is accessible through the EFB WISHBONE interface and can also be accessed through the SPI, I^2C, or JTAG interfaces.

Density Shifting

The MachXO3L/LF family has been designed to enable density migration within the same package. Furthermore, the architecture ensures a high success rate when performing design migration from lower density devices to higher density devices. In many cases, it is also possible to shift a lower utilization design targeted for a high-density device to a lower density device. However, the exact details of the final resource utilization will impact the likely success in each case. When migrating from lower to higher density or higher to lower density, ensure to review all the power supplies and NC pins of the chosen devices. For more details refer to the MachXO3 migration files.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
I_{IL}, I_{IH}[1, 4]	Input or I/O Leakage	Clamp OFF and $V_{CCIO} < V_{IN} < V_{IH}$ (MAX)	—	—	+175	µA
		Clamp OFF and $V_{IN} = V_{CCIO}$	–10	—	10	µA
		Clamp OFF and V_{CCIO} - 0.97 V < V_{IN} < V_{CCIO}	–175	—	—	µA
		Clamp OFF and 0 V < V_{IN} < V_{CCIO} - 0.97 V	—	—	10	µA
		Clamp OFF and V_{IN} = GND	—	—	10	µA
		Clamp ON and 0 V < $V_{IN} < V_{CCIO}$	—	—	10	µA
I_{PU}	I/O Active Pull-up Current	0 < V_{IN} < 0.7 V_{CCIO}	–30	—	–309	µA
I_{PD}	I/O Active Pull-down Current	V_{IL} (MAX) < $V_{IN} < V_{CCIO}$	30	—	305	µA
I_{BHLS}	Bus Hold Low sustaining current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	µA
I_{BHHS}	Bus Hold High sustaining current	$V_{IN} = 0.7V_{CCIO}$	–30	—	—	µA
I_{BHLO}	Bus Hold Low Overdrive current	0 ≤ V_{IN} ≤ V_{CCIO}	—	—	305	µA
I_{BHHO}	Bus Hold High Overdrive current	0 ≤ V_{IN} ≤ V_{CCIO}	—	—	–309	µA
V_{BHT}[3]	Bus Hold Trip Points		V_{IL} (MAX)	—	V_{IH} (MIN)	V
C1	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5	9	pf
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5.5	7	pf
V_{HYST}	Hysteresis for Schmitt Trigger Inputs[5]	V_{CCIO} = 3.3 V, Hysteresis = Large	—	450	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Large	—	250	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Large	—	125	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Large	—	100	—	mV
		V_{CCIO} = 3.3 V, Hysteresis = Small	—	250	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Small	—	150	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Small	—	60	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Small	—	40	—	mV

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25 °C, f = 1.0 MHz.
3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.
4. When V_{IH} is higher than V_{CCIO}, a transient current typically of 30 ns in duration or less with a peak current of 6mA can occur on the high-to-low transition. For true LVDS output pins in MachXO3L/LF devices, V_{IH} must be less than or equal to V_{CCIO}.
5. With bus keeper circuit turned on. For more details, refer to TN1280, MachXO3 sysIO Usage Guide.

sysIO Recommended Operating Conditions

Standard	V_{CCIO} (V)			V_{REF} (V)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
LVCMOS 3.3	3.135	3.3	3.465	—	—	—
LVCMOS 2.5	2.375	2.5	2.625	—	—	—
LVCMOS 1.8	1.71	1.8	1.89	—	—	—
LVCMOS 1.5	1.425	1.5	1.575	—	—	—
LVCMOS 1.2	1.14	1.2	1.26	—	—	—
LVTTL	3.135	3.3	3.465	—	—	—
LVDS25[1, 2]	2.375	2.5	2.625	—	—	—
LVDS33[1, 2]	3.135	3.3	3.465	—	—	—
LVPECL[1]	3.135	3.3	3.465	—	—	—
BLVDS[1]	2.375	2.5	2.625	—	—	—
MIPI[3]	2.375	2.5	2.625	—	—	—
MIPI_LP[3]	1.14	1.2	1.26	—	—	—
LVCMOS25R33	3.135	3.3	3.6	1.1	1.25	1.4
LVCMOS18R33	3.135	3.3	3.6	0.75	0.9	1.05
LVCMOS18R25	2.375	2.5	2.625	0.75	0.9	1.05
LVCMOS15R33	3.135	3.3	3.6	0.6	0.75	0.9
LVCMOS15R25	2.375	2.5	2.625	0.6	0.75	0.9
LVCMOS12R33[4]	3.135	3.3	3.6	0.45	0.6	0.75
LVCMOS12R25[4]	2.375	2.5	2.625	0.45	0.6	0.75
LVCMOS10R33[4]	3.135	3.3	3.6	0.35	0.5	0.65
LVCMOS10R25[4]	2.375	2.5	2.625	0.35	0.5	0.65

1. Inputs on-chip. Outputs are implemented with the addition of external resistors.
2. For the dedicated LVDS buffers.
3. Requires the addition of external resistors.
4. Supported only for inputs and BIDIs for -6 speed grade devices.

sysIO Single-Ended DC Electrical Characteristics[1, 2]

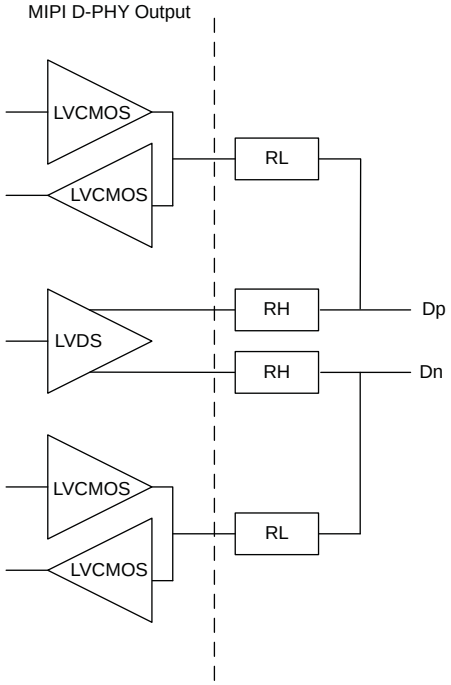
Input/Output Standard	V_{IL}		V_{IH}		V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL} Max.[4] (mA)	I_{OH} Max.[4] (mA)
	Min. (V)[3]	Max. (V)	Min. (V)	Max. (V)				
LVCMOS 3.3 LVTTL	–0.3	0.8	2.0	3.6	0.4	V_{CCIO} - 0.4	4	–4
							8	–8
							12	–12
							16	–16
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS 2.5	–0.3	0.7	1.7	3.6	0.4	V_{CCIO} - 0.4	4	–4
							8	–8
							12	–12
							16	–16
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS 1.8	–0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	V_{CCIO} - 0.4	4	–4
							8	–8
							12	–12
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS 1.5	–0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	V_{CCIO} - 0.4	4	–4
							8	–8
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS 1.2	–0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	V_{CCIO} - 0.4	4	–2
							8	–6
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS25R33	–0.3	VREF–0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS18R33	–0.3	VREF–0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS18R25	–0.3	VREF–0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS15R33	–0.3	VREF–0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS15R25	–0.3	VREF–0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS12R33	–0.3	VREF–0.1	VREF+0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS12R25	–0.3	VREF–0.1	VREF+0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain
LVCMOS10R33	–0.3	VREF–0.1	VREF+0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS10R25	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain

1. MachXO3L/LF devices allow LVCMOS inputs to be placed in I/O banks where V_{CCIO} is different from what is specified in the applicable JEDEC specification. This is referred to as a ratioed input buffer. In a majority of cases this operation follows or exceeds the applicable JEDEC specification. The cases where MachXO3L/LF devices do not meet the relevant JEDEC specification are documented in the table below.
2. MachXO3L/LF devices allow for LVCMOS referenced I/Os which follow applicable JEDEC specifications. For more details about mixed mode operation please refer to please refer to TN1280, MachXO3 sysIO Usage Guide.
3. The dual function I^2C pins SCL and SDA are limited to a V_{IL} min of –0.25 V or to –0.3 V with a duration of <10 ns.
4. For electromigration, the average DC current sourced or sinked by I/O pads between two consecutive VCCIO or GND pad connections, or between the last VCCIO or GND in an I/O bank and the end of an I/O bank, as shown in the Logic Signal Connections table (also shown as I/O grouping) shall not exceed a maximum of n * 8 mA. “n” is the number of I/O pads between the two consecutive bank VCCIO or GND connections or between the last VCCIO and GND in a bank and the end of a bank. IO Grouping can be found in the Data Sheet Pin Tables, which can also be generated from the Lattice Diamond software.

	Description	Min.	Typ.	Max.	Units
Low Power					
VCCIO	VCCIO of the Bank with LVCMOS12D 6 mA drive bidirectional IO buffer		1.2		V
VIH	Logic 1 input voltage	—	—	0.88	V
VIL	Logic 0 input voltage, not in ULP State	0.55	—	—	V
VHYST	Input hysteresis	25	—	—	mV

1. Over Recommended Operating Conditions

Figure 3-5. MIPI D-PHY Output Using External Resistors



Typical Building Block Function Performance – C/E Devices[1]

Pin-to-Pin Performance (LVCMOS25 12 mA Drive)

Function	–6 Timing	Units
Basic Functions		
16-bit decoder	8.9	ns
4:1 MUX	7.5	ns
16:1 MUX	8.3	ns

Register-to-Register Performance

Function	–6 Timing	Units
Basic Functions		
16:1 MUX	412	MHz
16-bit adder	297	MHz
16-bit counter	324	MHz
64-bit counter	161	MHz
Embedded Memory Functions		
1024x9 True-Dual Port RAM (Write Through or Normal, EBR output registers)	183	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (one PFU)	500	MHz

1. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.

Derating Logic Timing

Logic timing provided in the following sections of the data sheet and the Lattice design tools are worst case numbers in the operating range. Actual delays may be much faster. Lattice design tools can provide logic timing numbers at a particular temperature and voltage.

Parameter	Description	Device	–6		–5		Units
			Min.	Max.	Min.	Max.	
Generic DDRX1 Inputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX1_RX.SCLK.Aligned[8, 9]							
t_{DVA}	Input Data Valid After CLK	All MachXO3L/LF devices, all sides	—	0.317	—	0.344	UI
t_{DVE}	Input Data Hold After CLK		0.742	—	0.702	—	UI
f_{DATA}	DDRX1 Input Data Speed		—	300	—	250	Mbps
f_{DDRX1}	DDRX1 SCLK Frequency		—	150	—	125	MHz
Generic DDRX1 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX1_RX.SCLK.Centered[8, 9]							
t_{SU}	Input Data Setup Before CLK	All MachXO3L/LF devices, all sides	0.566	—	0.560	—	ns
t_{HO}	Input Data Hold After CLK		0.778	—	0.879	—	ns
f_{DATA}	DDRX1 Input Data Speed		—	300	—		Mbps
f_{DDRX1}	DDRX1 SCLK Frequency		—	150	—	125	MHz
Generic DDRX2 Inputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX2_RX.ECLK.Aligned[8, 9]							
t_{DVA}	Input Data Valid After CLK	MachXO3L/LF devices, bottom side only	—	0.316	—	0.342	UI
t_{DVE}	Input Data Hold After CLK		0.710	—	0.675	—	UI
f_{DATA}	DDRX2 Serial Input Data Speed		—	664	—	554	Mbps
f_{DDRX2}	DDRX2 ECLK Frequency		—	332	—	277	MHz
f_{SCLK}	SCLK Frequency		—	166	—	139	MHz
Generic DDRX2 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX2_RX.ECLK.Centered[8, 9]							
t_{SU}	Input Data Setup Before CLK	MachXO3L/LF devices, bottom side only	0.233	—	0.219	—	ns
t_{HO}	Input Data Hold After CLK		0.287	—	0.287	—	ns
f_{DATA}	DDRX2 Serial Input Data Speed		—	664	—	554	Mbps
f_{DDRX2}	DDRX2 ECLK Frequency		—	332	—	277	MHz
f_{SCLK}	SCLK Frequency		—	166	—	139	MHz
Generic DDR4 Inputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX4_RX.ECLK.Aligned[8]							
t_{DVA}	Input Data Valid After ECLK	MachXO3L/LF devices, bottom side only	—	0.307	—	0.320	UI
t_{DVE}	Input Data Hold After ECLK		0.782	—	0.699	—	UI
f_{DATA}	DDRX4 Serial Input Data Speed		—	800	—	630	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	400	—	315	MHz
f_{SCLK}	SCLK Frequency		—	100	—	79	MHz
Generic DDR4 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX4_RX.ECLK.Centered[8]							
t_{SU}	Input Data Setup Before ECLK	MachXO3L/LF devices, bottom side only	0.233	—	0.219	—	ns
t_{HO}	Input Data Hold After ECLK		0.287	—	0.287	—	ns
f_{DATA}	DDRX4 Serial Input Data Speed		—	800	—	630	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	400	—	315	MHz
f_{SCLK}	SCLK Frequency		—	100	—	79	MHz
7:1 LVDS Inputs (GDDR71_RX.ECLK.7:1)[9]							
t_{DVA}	Input Data Valid After ECLK	MachXO3L/LF devices, bottom side only	—	0.290	—	0.320	UI
t_{DVE}	Input Data Hold After ECLK		0.739	—	0.699	—	UI
f_{DATA}	DDR71 Serial Input Data Speed		—	756	—	630	Mbps
f_{DDR71}	DDR71 ECLK Frequency		—	378	—	315	MHz
f_{CLKIN}	7:1 Input Clock Frequency (SCLK) (minimum limited by PLL)		—	108	—	90	MHz

Figure 3-6. Receiver GDDR71_RX. Waveforms

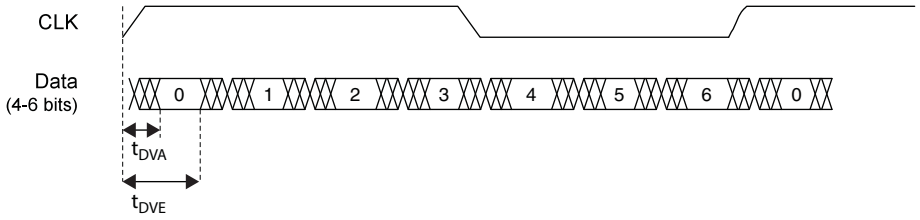
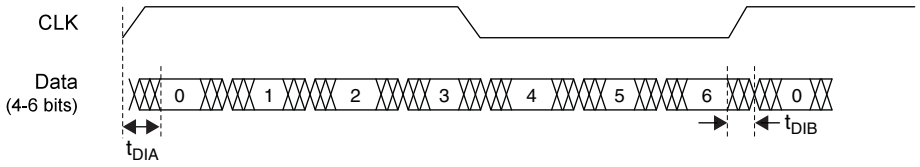


Figure 3-7. Transmitter GDDR71_TX. Waveforms



I²C Port Timing Specifications[1, 2]

Symbol	Parameter	Min.	Max.	Units
f_{MAX}	Maximum SCL clock frequency	—	400	kHz

1. MachXO3L/LF supports the following modes:
   • Standard-mode (Sm), with a bit rate up to 100 kbit/s (user and configuration mode)
   • Fast-mode (Fm), with a bit rate up to 400 kbit/s (user and configuration mode)
2. Refer to the I²C specification for timing requirements.

SPI Port Timing Specifications[1]

Symbol	Parameter	Min.	Max.	Units
f_{MAX}	Maximum SCK clock frequency	—	45	MHz

1. Applies to user mode only. For configuration mode timing specifications, refer to sysCONFIG Port Timing Specifications table in this data sheet.

Switching Test Conditions

Figure 3-9 shows the output test load used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-6.

Figure 3-9. Output Test Load, LVTTL and LVCMOS Standards

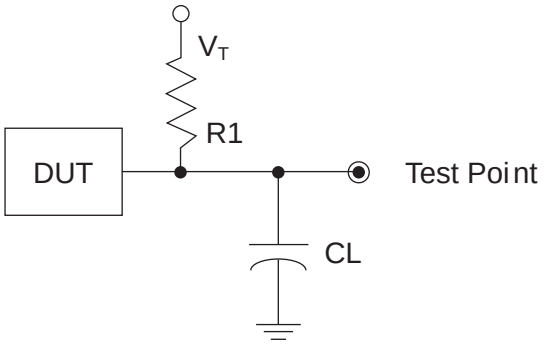


Table 3-6. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R1	CL	Timing Ref.	VT
LVTTL and LVCMOS settings (L -> H, H -> L)	∞	0pF	LVTTL, LVCMOS 3.3 = 1.5 V	—
			LVCMOS 2.5 = $V_{CCIO}/2$	—
			LVCMOS 1.8 = $V_{CCIO}/2$	—
			LVCMOS 1.5 = $V_{CCIO}/2$	—
			LVCMOS 1.2 = $V_{CCIO}/2$	—
LVTTL and LVCMOS 3.3 (Z -> H)	188	0pF	1.5	V_{OL}
LVTTL and LVCMOS 3.3 (Z -> L)			1.5	V_{OH}
Other LVCMOS (Z -> H)			$V_{CCIO}/2$	V_{OL}
Other LVCMOS (Z -> L)			$V_{CCIO}/2$	V_{OH}
LVTTL + LVCMOS (H -> Z)			V_{OH} - 0.15	V_{OL}
LVTTL + LVCMOS (L -> Z)			V_{OL} - 0.15	V_{OH}

Note: Output test conditions for all other interfaces are determined by the respective standards.

MachXO3 Family Data Sheet Ordering Information

May 2016 Advance Data Sheet DS1047

MachXO3 Part Number Description

LCMXO3X – XXXXX – XXXXXXX XX

Device Family
- Low Density MachXO3 FPGA

Configuration Memory
- L = NVCM
- LF = Flash

Logic Capacity
- 640 = 640 LUTs
- 1300 = 1280 LUTs
- 2100 = 2112 LUTs
- 4300 = 4320 LUTs
- 6900 = 6864 LUTs
- 9400 = 9400 LUTs

Supply Voltage
- C = 2.5 V / 3.3 V
- E = 1.2 V

Speed
- 5 = Slowest
- 6 = Fastest

Package
- UWG36 = 36-Ball Halogen-Free WLCSP (0.4 mm Pitch)
- UWG49 = 49-Ball Halogen-Free WLCSP (0.4 mm Pitch)
- UWG81 = 81-Ball Halogen-Free WLCSP (0.4 mm Pitch)
- MG121 = 121-Ball Halogen-Free csfBGA (0.5 mm Pitch)
- MG256 = 256-Ball Halogen-Free csfBGA (0.5 mm Pitch)
- MG324 = 324-Ball Halogen-Free csfBGA (0.5 mm Pitch)
- BG256 = 256-Ball Halogen-Free caBGA (0.8 mm Pitch)
- BG324 = 324-Ball Halogen-Free caBGA (0.8 mm Pitch)
- BG400 = 400-Ball Halogen-Free caBGA (0.8 mm Pitch)
- BG484 = 484-Ball Halogen-Free caBGA (0.8 mm Pitch)

Grade
- C = Commercial
- I = Industrial

Shipping Method
- Blank = Trays
- TR = Tape and Reel
- TR50 = WLCSP Package, 50 parts per reel
- TR1K = WLCSP Package, 1,000 parts per reel

Ordering Information

MachXO3L/LF devices have top-side markings as shown in the examples below, on the 256-Ball caBGA package with MachXO3-6900 device in Commercial Temperature in Speed Grade 5. Notice that for the MachXO3LF device, *LMXO3LF* is used instead of *LCMXO3LF* as in the Part Number.

Note: *LCMXO3LF* is marked with *LMXO3LF*

Note: Markings are abbreviated for small packages.

MachXO3LF Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-640E-5MG121C	640	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3LF-640E-6MG121C	640	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3LF-640E-5MG121I	640	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3LF-640E-6MG121I	640	1.2 V	6	Halogen-Free csfBGA	121	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-1300E-5UWG36CTR	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3LF-1300E-5UWG36CTR50	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3LF-1300E-5UWG36CTR1K	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3LF-1300E-5UWG36ITR	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3LF-1300E-5UWG36ITR50	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3LF-1300E-5UWG36ITR1K	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3LF-1300E-5MG121C	1300	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3LF-1300E-6MG121C	1300	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3LF-1300E-5MG121I	1300	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3LF-1300E-6MG121I	1300	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3LF-1300E-5MG256C	1300	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3LF-1300E-6MG256C	1300	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3LF-1300E-5MG256I	1300	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3LF-1300E-6MG256I	1300	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3LF-1300C-5BG256C	1300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3LF-1300C-6BG256C	1300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3LF-1300C-5BG256I	1300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3LF-1300C-6BG256I	1300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-2100E-5UWG49CTR	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3LF-2100E-5UWG49CTR50	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3LF-2100E-5UWG49CTR1K	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3LF-2100E-5UWG49ITR	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3LF-2100E-5UWG49ITR50	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3LF-2100E-5UWG49ITR1K	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3LF-2100E-5MG121C	2100	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3LF-2100E-6MG121C	2100	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3LF-2100E-5MG121I	2100	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3LF-2100E-6MG121I	2100	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3LF-2100E-5MG256C	2100	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3LF-2100E-6MG256C	2100	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3LF-2100E-5MG256I	2100	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3LF-2100E-6MG256I	2100	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3LF-2100E-5MG324C	2100	1.2 V	5	Halogen-Free csfBGA	324	COM
LCMXO3LF-2100E-6MG324C	2100	1.2 V	6	Halogen-Free csfBGA	324	COM
LCMXO3LF-2100E-5MG324I	2100	1.2 V	5	Halogen-Free csfBGA	324	IND

Date	Version	Section	Change Summary
September 2015	1.5	DC and Switching Characteristics	Updated the MIPI D-PHY Emulation section. Revised Table 3-5, MIPI D-PHY Output DC Conditions. — Revised RL Typ. value. — Revised RH description and values.
			Updated the Maximum sysIO Buffer Performance section. Revised MIPI Max. Speed value.
			Updated the MachXO3L/LF External Switching Characteristics – C/E Devices section. Added footnotes 14 and 15.
August 2015	1.4	Architecture	Updated the Device Configuration section. Added JTAGENB to TAP dual purpose pins.
		Ordering Information	Updated the top side markings section to indicate the use of LMXO3LF for the LCMXO3LF device.
March 2015	1.3	All	General update. Added MachXO3LF devices.
October 2014	1.2	Introduction	Updated Table 1-1, MachXO3L Family Selection Guide. Revised XO3L-2100 and XO3L-4300 IO for 324-ball csfBGA package.
		Architecture	Updated the Dual Boot section. Corrected information on where the primary bitstream and the golden image must reside.
		Pinout Information	Updated the Pin Information Summary section. Changed General Purpose IO Bank 5 values for MachXO3L-2100 and MachXO3L-4300 CSFBGA 324 package. Changed Number 7:1 or 8:1 Gearboxes for MachXO3L-640 and MachXO3L-1300. Removed DQS Groups (Bank 1) section. Changed VCCIO Pins Bank 1 values for MachXO3L-1300, MachXO3L-2100, MachXO3L-4300 and MachXO3L-6900 CSFBGA 256 package. Changed GND values for MachXO3L-1300, MachXO3L-2100, MachXO3L-4300 and MachXO3L-6900 CSFBGA 256 package. Changed NC values for MachXO3L-2100 and MachXO3L-4300 CSFBGA 324 package.
		DC and Switching Characteristics	Updated the BLVDS section. Changed output impedance nominal values in Table 3-2, BLVDS DC Condition.
			Updated the LVPECL section. Changed output impedance nominal value in Table 3-3, LVPECL DC Condition.
			Updated the sysCONFIG Port Timing Specifications section. Updated INITN low time values.
July 2014	1.1	DC and Switching Characteristics	Updated the Static Supply Current – C/E Devices section. Added devices.
			Updated the Programming and Erase Supply Current – C/E Device section. Added devices.
			Updated the sysIO Single-Ended DC Electrical Characteristics section. Revised footnote 4.
			Added the NVCM Download Time section.
			Updated the Typical Building Block Function Performance – C/E Devices section. Added information to footnote.
		Pinout Information	Updated the Pin Information Summary section.
		Ordering Information	Updated the MachXO3L Part Number Description section. Added packages.
			Updated the Ordering Information section. General update.